

TIP110/111/112

Monolithic Construction With Built In Base-Emitter Shunt Resistors

- Complementary to TIP115/116/117
- High DC Current Gain : h_{FE}=1000 @ V_{CE}=4V, I_C=1A(Min.)
- Low Collector-Emitter Saturation Voltage
- Industrial Use

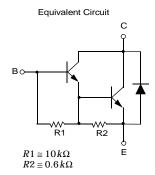


1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage : TIP110	60	V	
	: TIP111	80	V	
	: TIP112	100	V	
	Collector-Emitter Voltage : TIP110	60	V	
V_{CEO}	: TIP111	80	V	
	: TIP112	100	V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current (DC)	2	Α	
I _{CP}	Collector Current (Pulse)	4	Α	
I _B	Base Current (DC)	50	mA	
P _C	Collector Dissipation (T _a =25°C)	2	W	
	Collector Dissipation (T _C =25°C)	50	W	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 65 ~ 150	°C	



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage				
	: TIP110	$I_C = 30 \text{mA}, I_B = 0$	60		V
	: TIP111		80		V
	: TIP112		100		V
I _{CEO}	Collector Cut-off Current				
	: TIP110	$V_{CE} = 30V, I_{B} = 0$		2	mA
	: TIP111	$V_{CE} = 40V, I_{B} = 0$		2	mA
	: TIP112	$V_{CE} = 50V, I_{B} = 0$		2	mA
I _{CBO}	Collector Cut-off Current				
	: TIP110	$V_{CB} = 60V, I_{E} = 0$		1	mA
	: TIP111	$V_{CB} = 80V, I_{E} = 0$		1	mA
	: TIP112	$V_{CB} = 100V, I_{E} = 0$		1	mA
I _{EBO}	Emitter Cut-off Current	$V_{BE} = 5V, I_{C} = 0$		2	mA
h _{FE}	DC Current Gain	$V_{CE} = 4V, I_{C} = 1A$	1000		
		$V_{CE} = 4V, I_{C} = 2A$	500		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 2A, I_B = 8mA$		2.5	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = 4V$, $I_{C} = 2A$		2.8	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 0.1MHz$		100	pF

Typical Characteristics

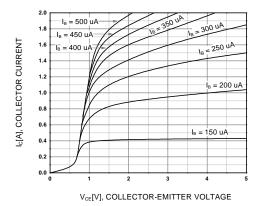


Figure 1. Static Characteristic

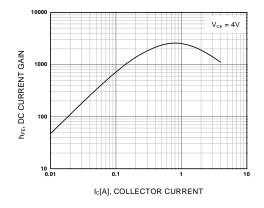


Figure 2. DC current Gain

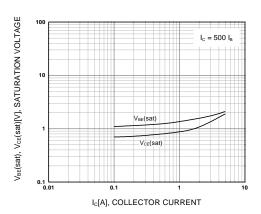


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

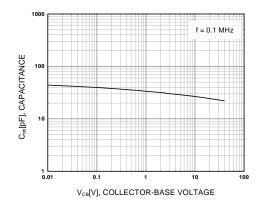


Figure 4. Collector Output Capacitance

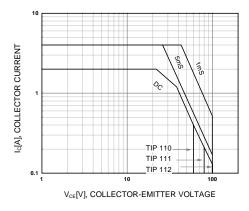


Figure 5. Safe Operating Area

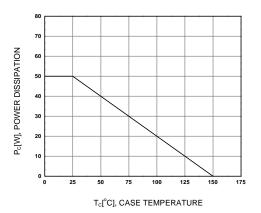


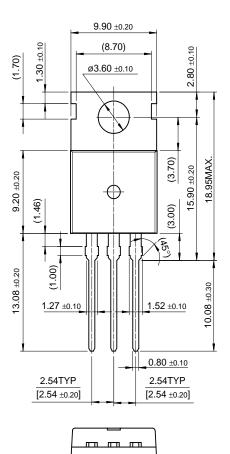
Figure 6. Power Derating

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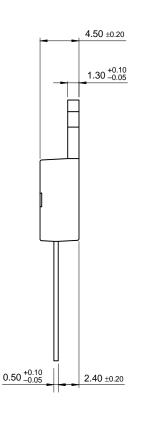
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Package Demensions

TO-220



 10.00 ± 0.20



Dimensions in Millimeters

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